

Overview of the XRTC Single-Event Test Results on the Xilinx 7-Series FPGAs

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- Introduction and Background
 - Comments on Commercial Parts Use in Space
 - Xilinx Radiation Test Consortium
- Four Recent Papers
 - E. Crabill (Xilinx) on SEM-IP at SELSE
 - × Available at: http://softerrors.info/selse/images/selse_2014/papers/selse_2014_13_paper.pdf
 - D.S.Lee (Sandia) on Kintex-7 SEE at NREC REDW
 - × Proceedings in press; preprints on request.
 - G.M.Swift (SwiftERS) K-7 Current Steps at MAPLD
 - Prof. M.Wirthlin (BYU) on CRAM MBU/MCUs at NSREC
 - × In review cycle for TNS Dec 2014

- “Right” reasons
 - Speed
 - Size
 - Power
 - More I/O
- WRONG Reason
 - Cost
 - Be prepared for lots of expensive testing and waiving requirements and operational difficulties

XRTC Setup Evolution

000 2001 2002 2003 2004 2005 2006 2007 2008 2009 2010 2011 2

Virtex-2

Virtex-IIpro

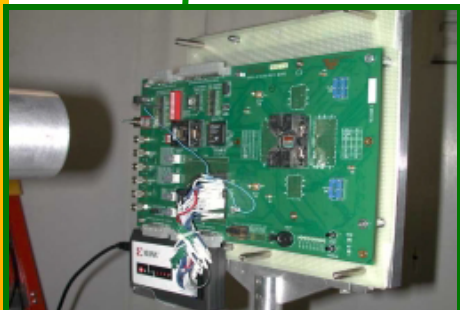
Virtex-4

Virtex-5

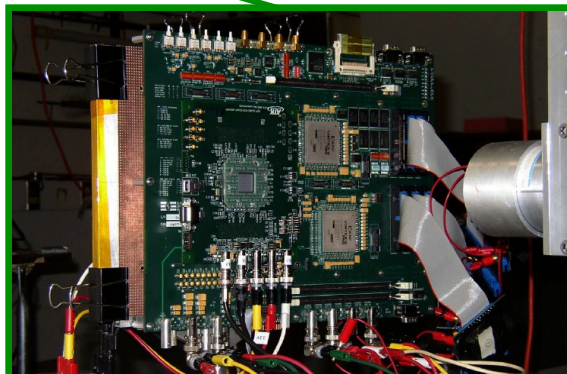
JPL & Xilinx
partner up

1st Annual
Meeting

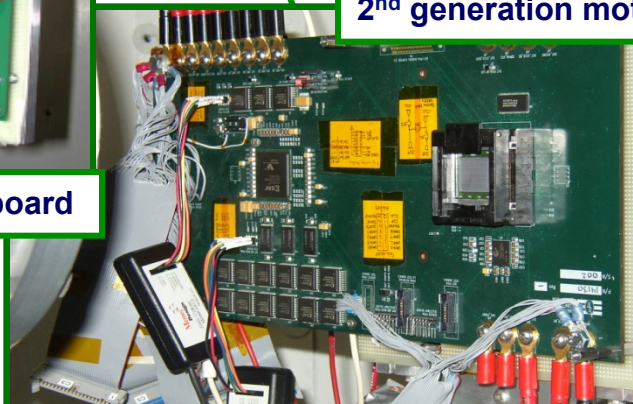
Consortium
formation



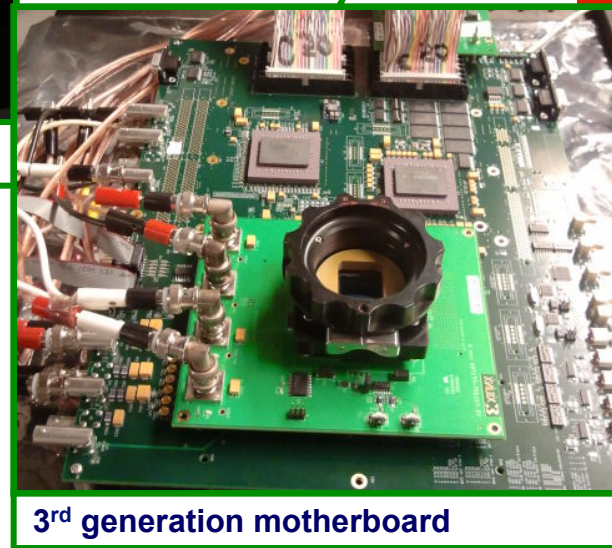
0th generation motherboard



2nd generation motherboard



1st generation motherboard



3rd generation motherboard

Upset Results Overview

- Configuration Upsets
less than 100 per day
- BRAM Upsets (100% use)
less than 50 per day
- Flip-flop Upsets (100% use)
less than 1 per week

Investigation of High Current Events in 28nm 7-Series FPGAs

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- Introduction
 - DUT - 7-Series
 - Review of Latchup Basics
- Test Setup
- Observed: Single-event Current Steps ???
- Possible Explanations
- Working Hypothesis:
 - Latchup with Significant Series Resistance
- Mitigation Ideas and Future Work

7 Series Xilinx FPGAs

- Current generation is 28 nm, TSMC process
- Four families
 - Artix – high volume FPGA
 - Kintex – mid-range FPGA
 - Virtex – high performance FPGA
 - Zynq – high-performance dual ARM processors
plus large FPGA fabric and I/Os

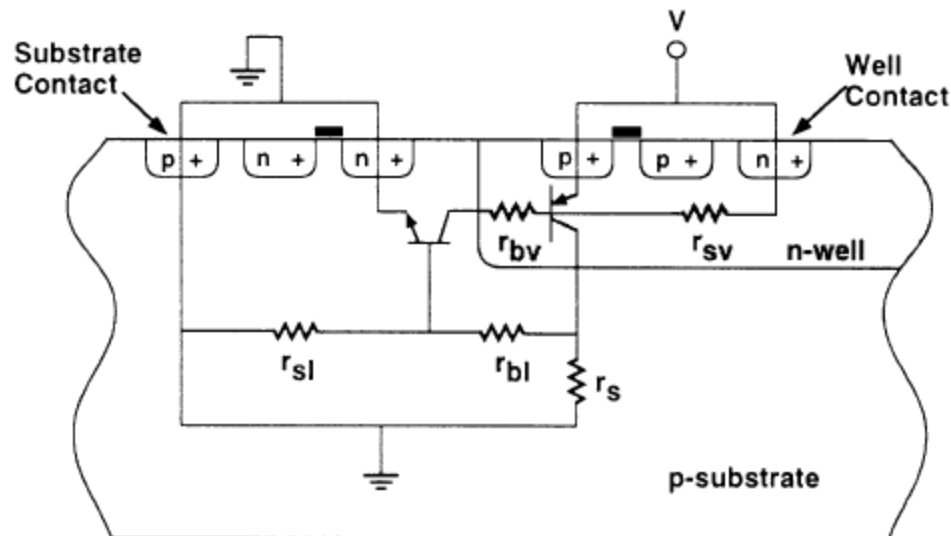
Latchup Basics

- SCR-like action, due to parasitic bipolar transistors
- All CMOS inherently susceptible
- Can be suppressed by reducing carrier lifetime
- May be destructive or cause latent damage (or not)

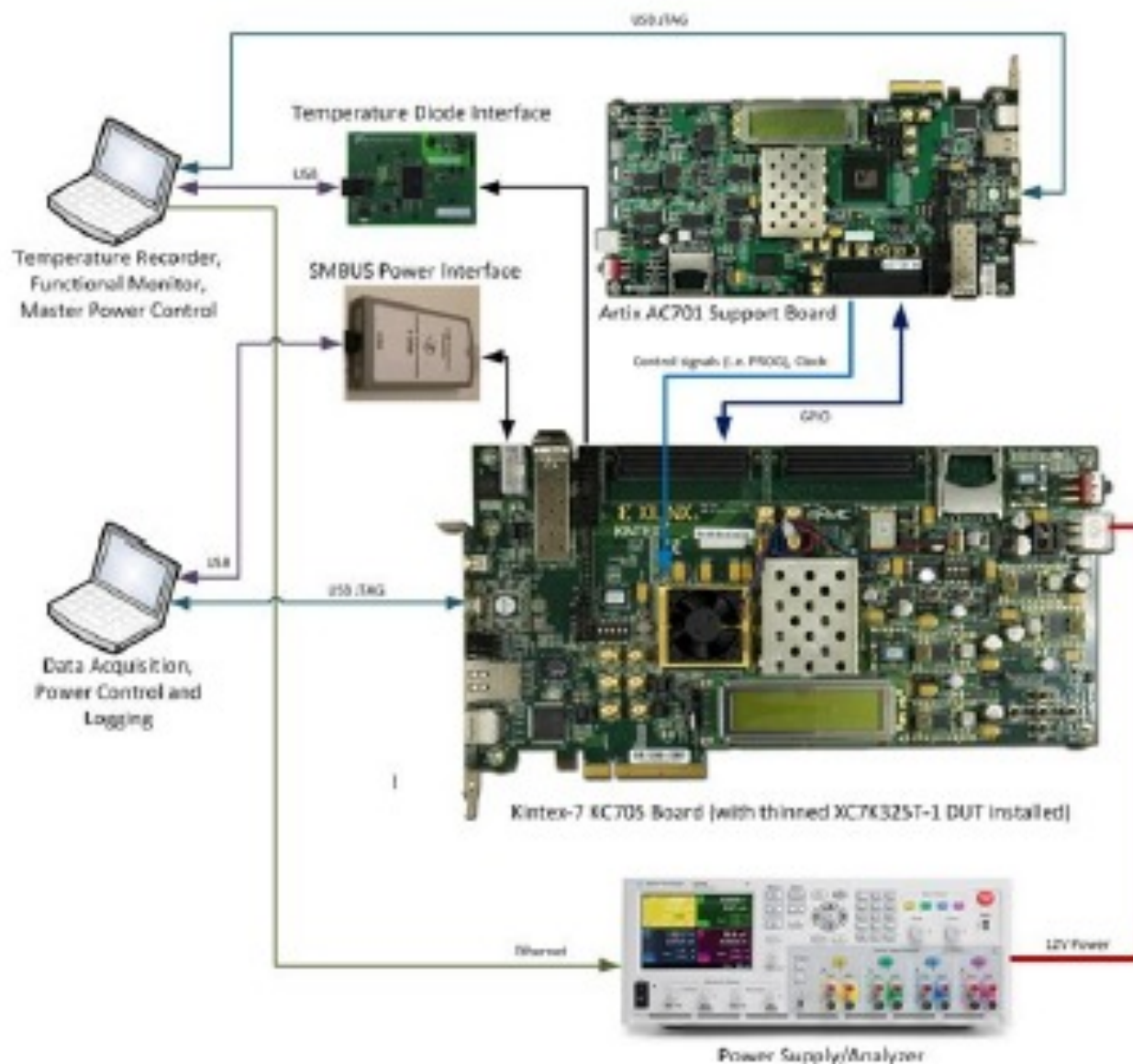
Latchup's I-V Characteristics

Gain of two transistors > 1 causes regenerative feedback resulting in runaway current

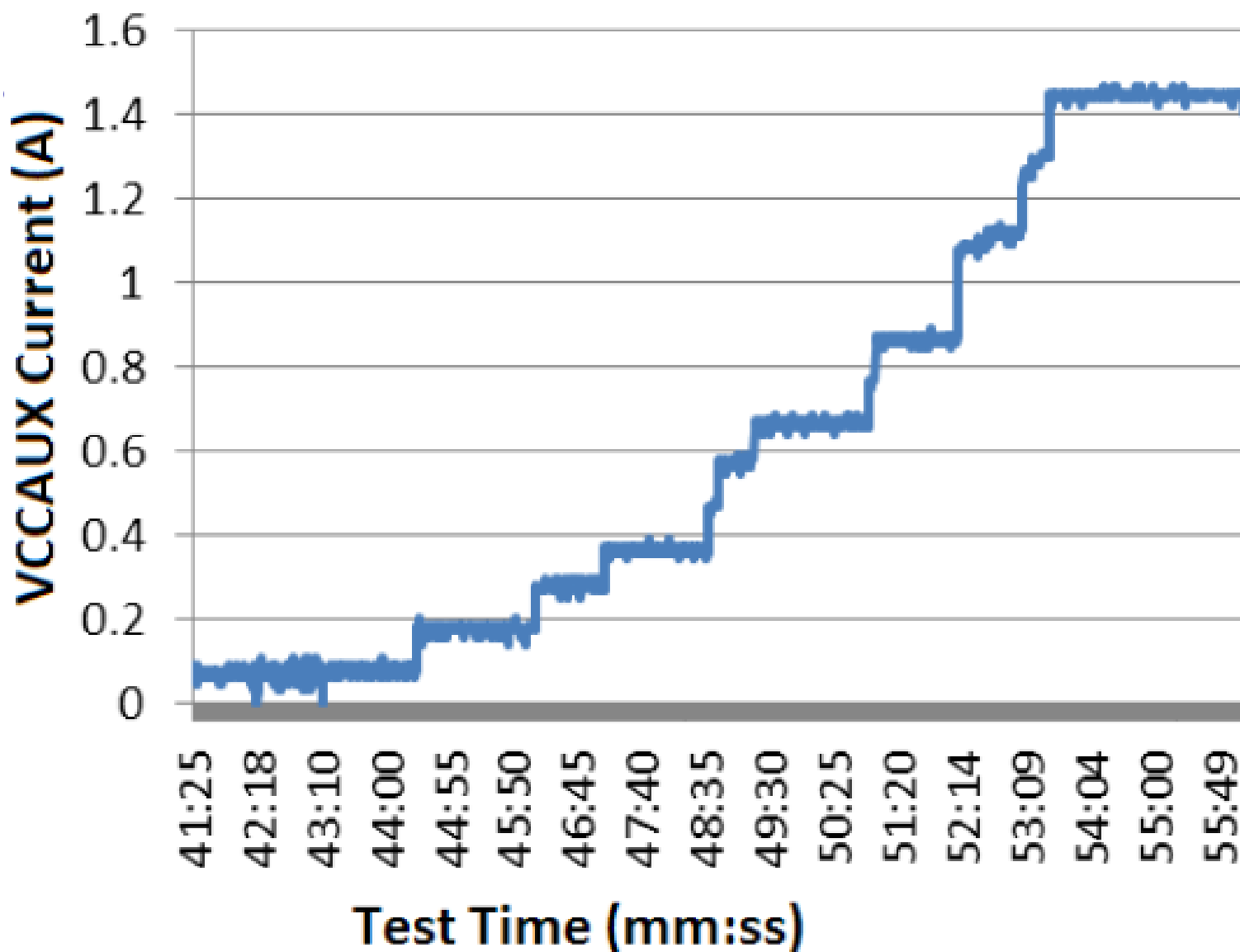
In latchup, lowering the voltage lowers transistor gain; below “holding voltage” gain < 1 releasing the latchup







Test Setup



Current Steps on Vaux



Observed Characteristics

- No functional problems observed
- What restores nominal current?
 -  Resetting user circuit does not
 -  Scrubbing configuration does not
 -  Reconfiguring device does not
 -  Power cycle does
- Distribution of current step sizes*
 - 105 mA average, 25 mA std.deviation at room temp.
 - 125 mA average, 40 mA std.dev at elevated temp.
- Higher cross section at high temperature

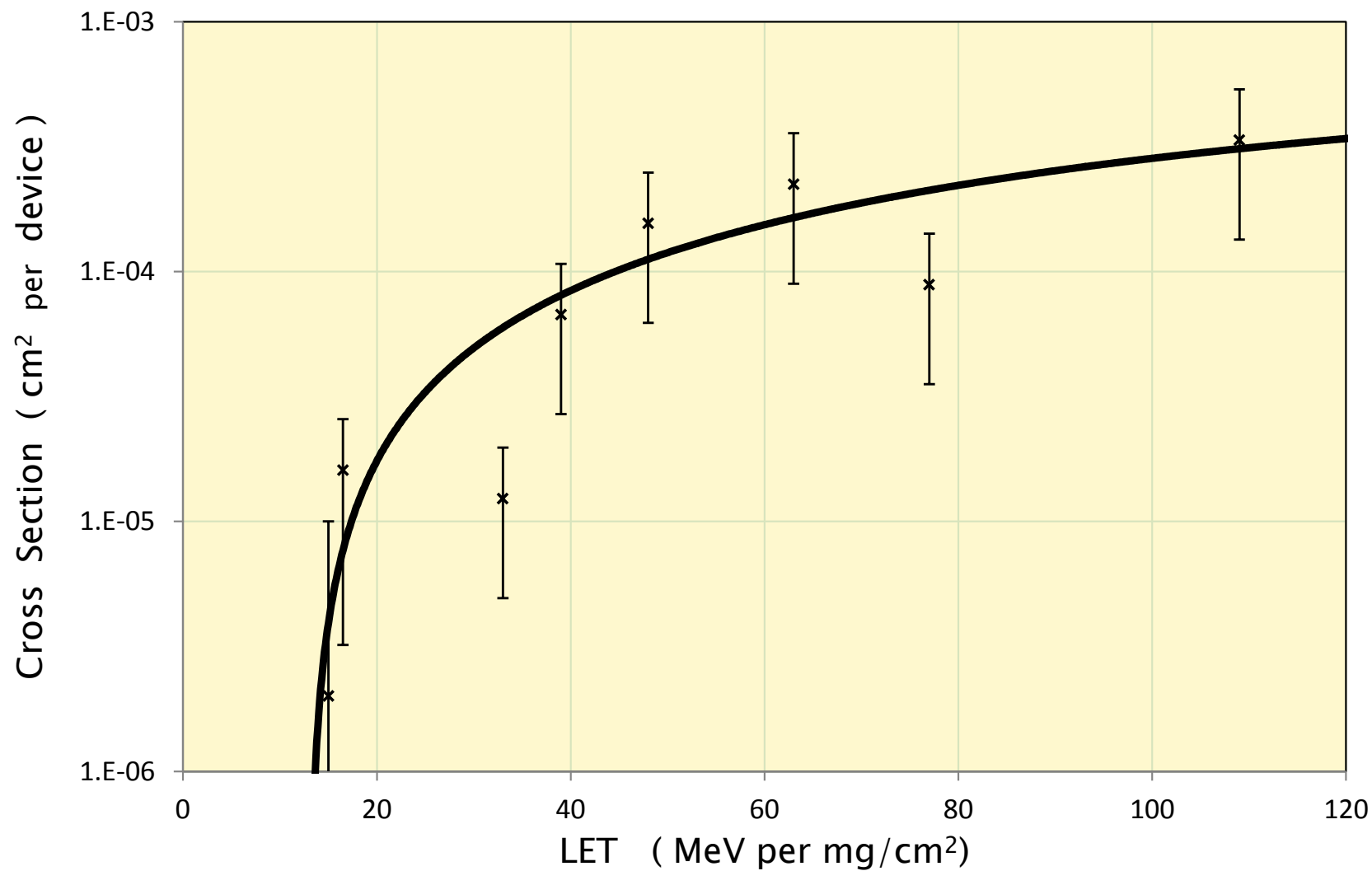
* Baseline is 80 mA and 210 mA for the two test designs used

Powered by Vaux = 1.8V

Vaux powers “mfg” level misc’ l functions

- Configuration engine
- Efuse programming
- XADC (previous name: ‘system monitor’)
- I/O pin optional function(s)
 -
 -
 -


Measured Susceptibility



Is it latchup?

 No functional problem observed

 Only fix is power cycle

 Current step size, roughly 100 mA

- Note this implies 18 ohms impedance

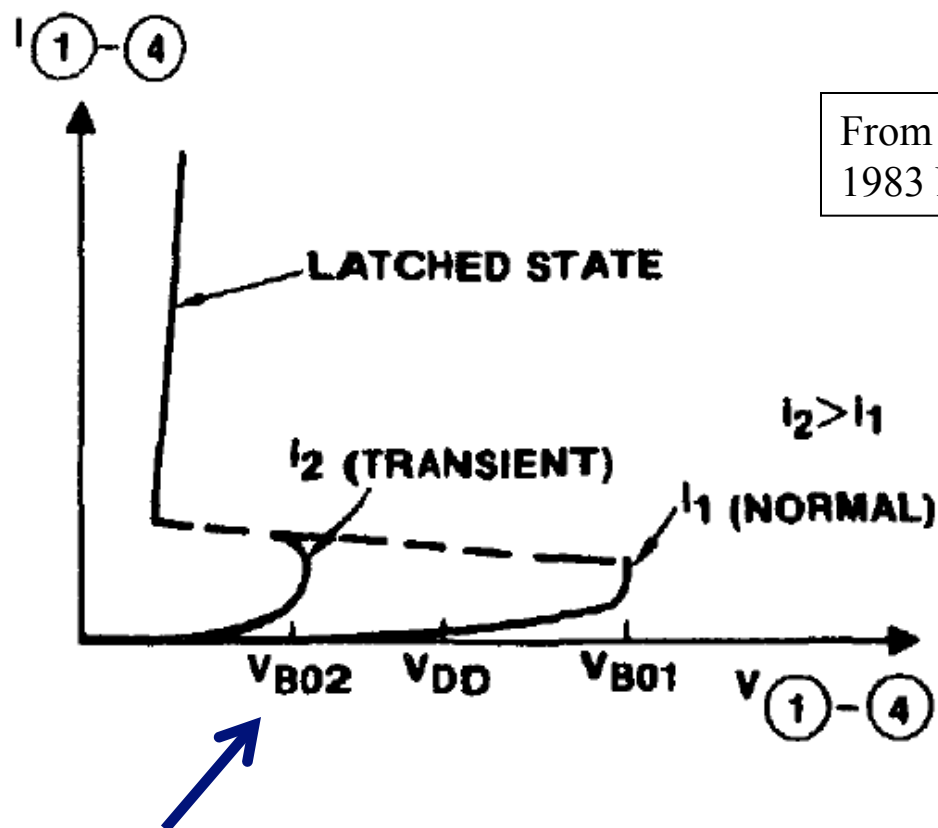
 Worse at elevated temperature

What else can it be?

- Upset-induced internal contention
 - ✗ Current too big
 - ✗ Typical contention current is < 0.5 mA
- Dielectric Rupture
 - ✗ Power cycle restores nominal current
- Snapback
 - ?

Additional Experiment

Current steps exhibit a holding voltage signature



From J. Pickell,
1983 NSREC Short Course Notes

Holding voltage is between 1.20V and 1.25V

What are current steps ??

- Working hypothesis –
Latchup with series impedance
- More questions –
 - What's acting as the current limiting resistor ?
 - Where are the high current sites on the die ?
 - What circuit function(s) is/are involved ?
 - Is this the mythical creature: micro-latchup ?Most important of all:
 - How to prove it's non-destructive, non-damaging

Results Update

NASA/Goddard confirms they've seen these current steps

- The XADC block is likely culprit, Melanie Berg hypothesized
New XRTC test results from Berkeley (6/20/14) show XADC is not a source of these single-event current steps
- With separated XADC power from Vaux,
 - × Current steps are only observed on Vaux
- With XADC turned off via control bit and powered with 0.7 V (well below the holding voltage),
 - × The measured cross section did not change at LET=41
 - 20 events vs. 21 events for fluence of $6.0 \times 10^5 / \text{cm}^2$

JPL test results from Indiana (July 2014) with

200 MeV protons: NO proton-induced current steps.

Possible Future Work

- Localize structure involved
 - In-situ, thorough electrical “wring-out” test
 - Collimators (millimeter resolution)
 - Infra-red camera (ten micrometer resolution)
 - Micro-beam (few micrometer resolution)
 - Laser (micrometer resolution)
- Pursue damage questions
 - Do irradiated DUTs pass full production test ?
 - What’ s the current density? Is it capable of producing damage?
 - Do irradiated DUTs pass accelerated life testing?

If it is low-current latchup,

- Any SEL is scary to fly, but
 - × The rate's really low (GEO: 1 in 5-20 years)
 - × No obvious functionality problems or damage
- Mitigation options (though not very attractive)
 - × Running with Vaux below spec. min. reduces rate
 - × Minimizing time in SEL lowers damage risk
 - × Test neutron irradiated part
- Proving non-destructiveness is very difficult

Further investigation is needed